

IRFP17N50L

SMPS MOSFET

HEXFET® Power MOSFET

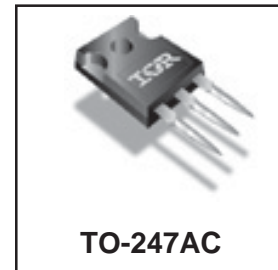
Applications

- Zero Voltage Switching SMPS
- Telecom and Server Power Supplies
- Uninterruptible Power Supplies
- Motor Control applications

V_{DSS}	$R_{DS(on)}$ typ.	T_{rr} typ.	I_D
500V	0.28Ω	170ns	16A

Features and Benefits

- SuperFast body diode eliminates the need for external diodes in ZVS applications.
- Lower Gate charge results in simpler drive requirements.
- Enhanced dv/dt capabilities offer improved ruggedness.
- Higher Gate voltage threshold offers improved noise immunity.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	16	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	11	
I_{DM}	Pulsed Drain Current ①	64	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	220	W
	Linear Derating Factor	1.8	W/°C
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ②	19	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	16	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	64		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}$, $I_S = 16\text{A}$, $V_{GS} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	170	250	ns	$T_J = 25^\circ\text{C}$, $I_F = 16\text{A}$
		—	220	330		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
Q_{rr}	Reverse Recovery Charge	—	470	710	nC	$T_J = 25^\circ\text{C}$, $I_S = 16\text{A}$, $V_{GS} = 0\text{V}$ ④
		—	810	1210		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
I_{RRM}	Reverse Recovery Current	—	7.3	11	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

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Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	500	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.60	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	0.28	0.32	Ω	V _{GS} = 10V, I _D = 9.9A ④
V _{GS(th)}	Gate Threshold Voltage	3.0	—	5.0	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	50	μA	V _{DS} = 500V, V _{GS} = 0V
		—	—	2.0	mA	V _{DS} = 400V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 30V
	Gate-to-Source Reverse Leakage	—	—	-100	nA	V _{GS} = -30V
R _G	Internal Gate Resistance	—	1.4	—	Ω	f = 1MHz, open drain

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	11	—	—	S	V _{DS} = 50V, I _D = 9.9A
Q _g	Total Gate Charge	—	—	130	nC	I _D = 16A V _{DS} = 400V V _{GS} = 10V, See Fig. 7 & 15 ④
Q _{gs}	Gate-to-Source Charge	—	—	33		
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	59		
t _{d(on)}	Turn-On Delay Time	—	21	—	ns	V _{DD} = 250V I _D = 16A R _G = 7.5Ω V _{GS} = 10V, See Fig. 14a & 14b ④
t _r	Rise Time	—	51	—		
t _{d(off)}	Turn-Off Delay Time	—	50	—		
t _f	Fall Time	—	28	—		
C _{iss}	Input Capacitance	—	2760	—	pF	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz, See Fig. 5 V _{GS} = 0V, V _{DS} = 1.0V, f = 1.0MHz V _{GS} = 0V, V _{DS} = 400V, f = 1.0MHz V _{GS} = 0V, V _{DS} = 0V to 400V ⑤
C _{oss}	Output Capacitance	—	325	—		
C _{rss}	Reverse Transfer Capacitance	—	37	—		
C _{oss}	Output Capacitance	—	3690	—		
C _{oss}	Output Capacitance	—	84	—		
C _{oss eff.}	Effective Output Capacitance	—	159	—		
C _{oss eff. (ER)}	Effective Output Capacitance (Energy Related)	—	120	—		

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ⑥	—	390	mJ
I _{AR}	Avalanche Current ①	—	16	A
E _{AR}	Repetitive Avalanche Energy ①	—	22	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ⑥	—	0.56	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.24	—	
R _{θJA}	Junction-to-Ambient ⑥	—	40	

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- ② Starting T_J = 25°C, L = 3.0mH, R_G = 25Ω, I_{AS} = 16A. (See Figure 12).
- ③ I_{SD} = 16A, di/dt ≤ 230A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C.

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ C_{oss eff.} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

C_{oss eff.(ER)} is a fixed capacitance that stores the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

⑥ R_θ is measured at T_J approximately 90°C

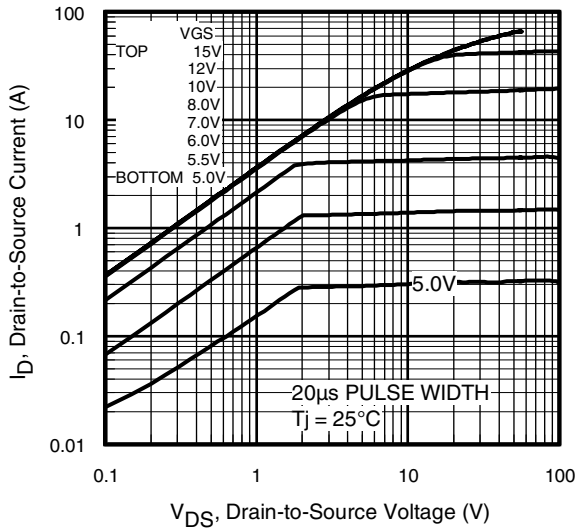


Fig 1. Typical Output Characteristics

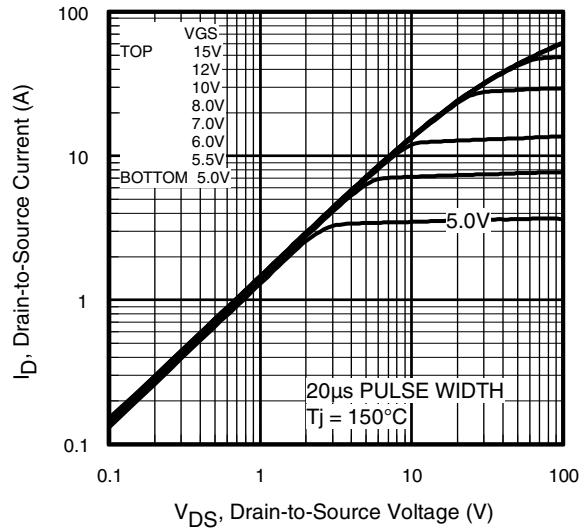


Fig 2. Typical Output Characteristics

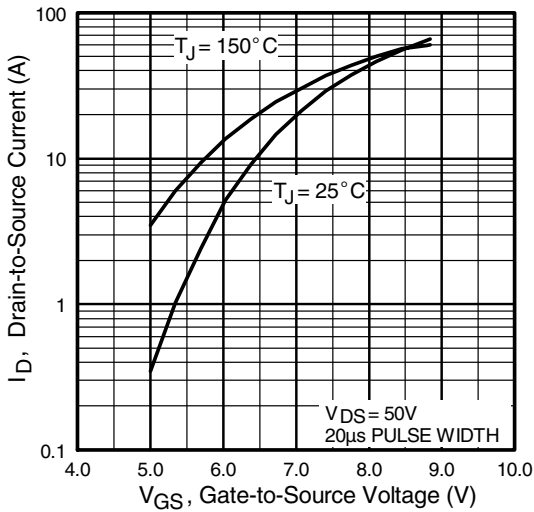


Fig 3. Typical Transfer Characteristics

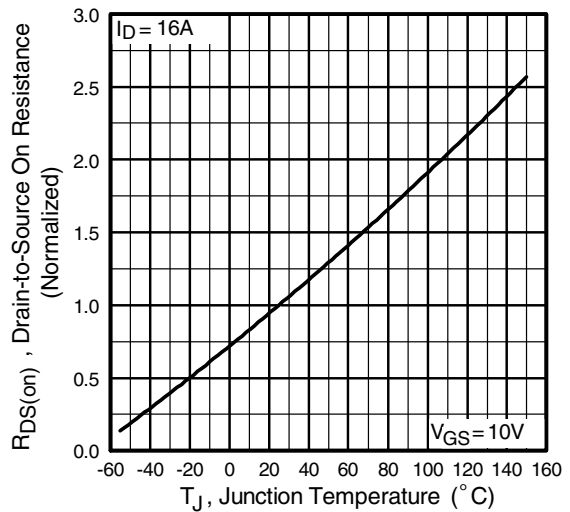


Fig 4. Normalized On-Resistance Vs. Temperature

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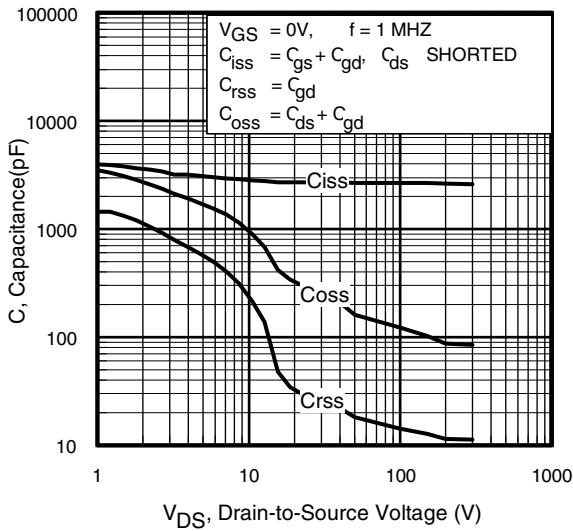


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

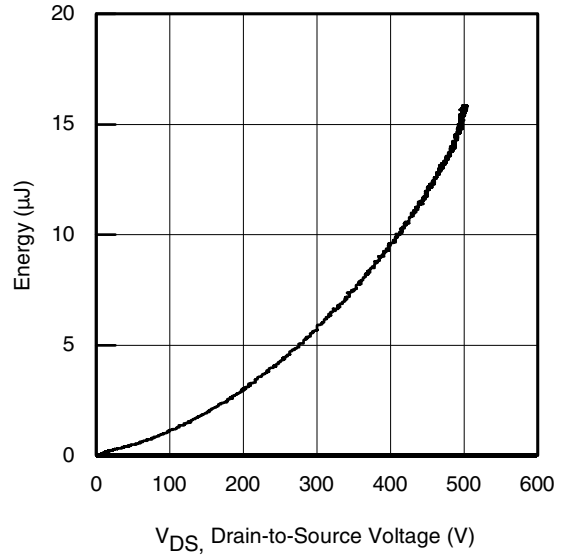


Fig 6. Typ. Output Capacitance Stored Energy vs. V_{DS}

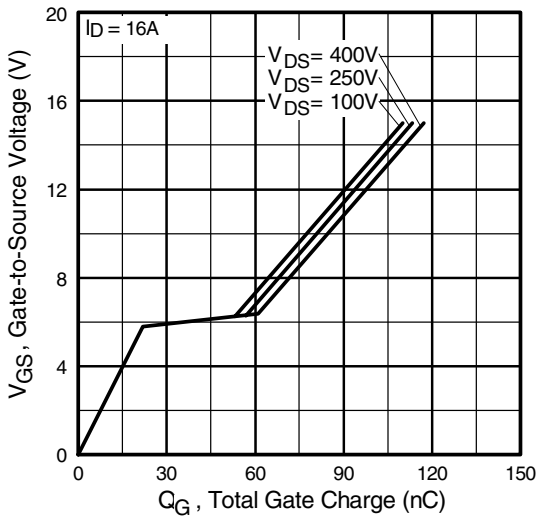


Fig 7. Typical Gate Charge Vs. Gate-to-Source Voltage

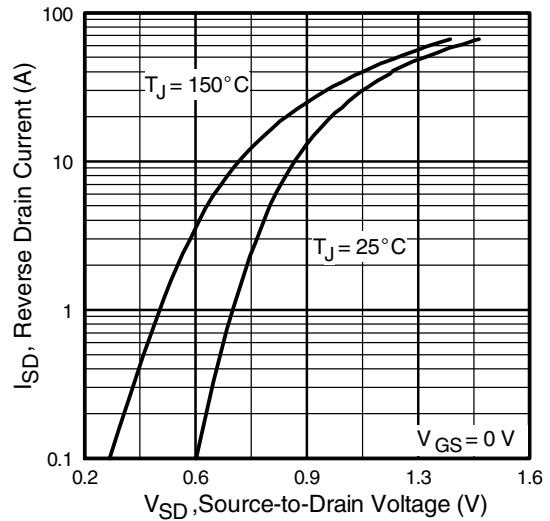


Fig 8. Typical Source-Drain Diode Forward Voltage

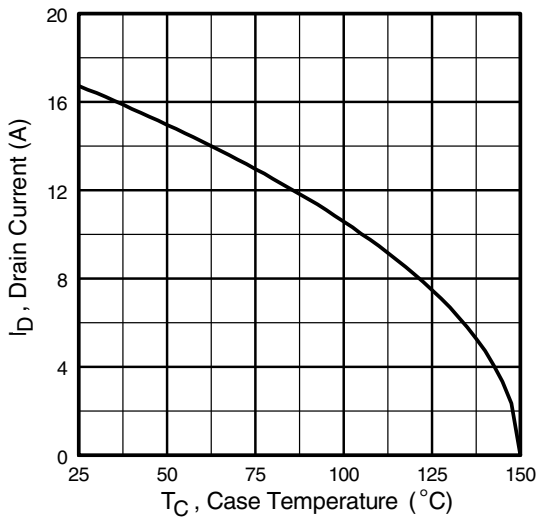


Fig 9. Maximum Drain Current Vs. Case Temperature

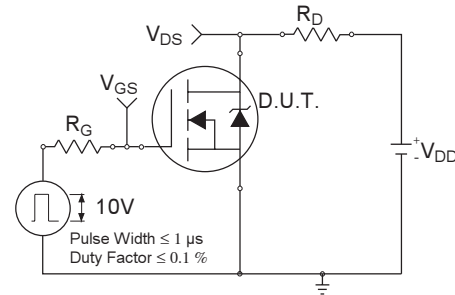


Fig 10a. Switching Time Test Circuit

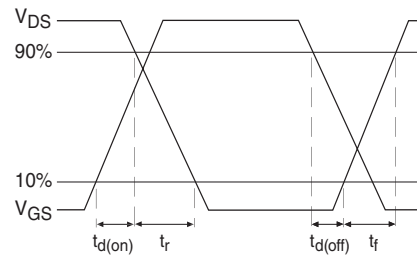


Fig 10b. Switching Time Waveforms

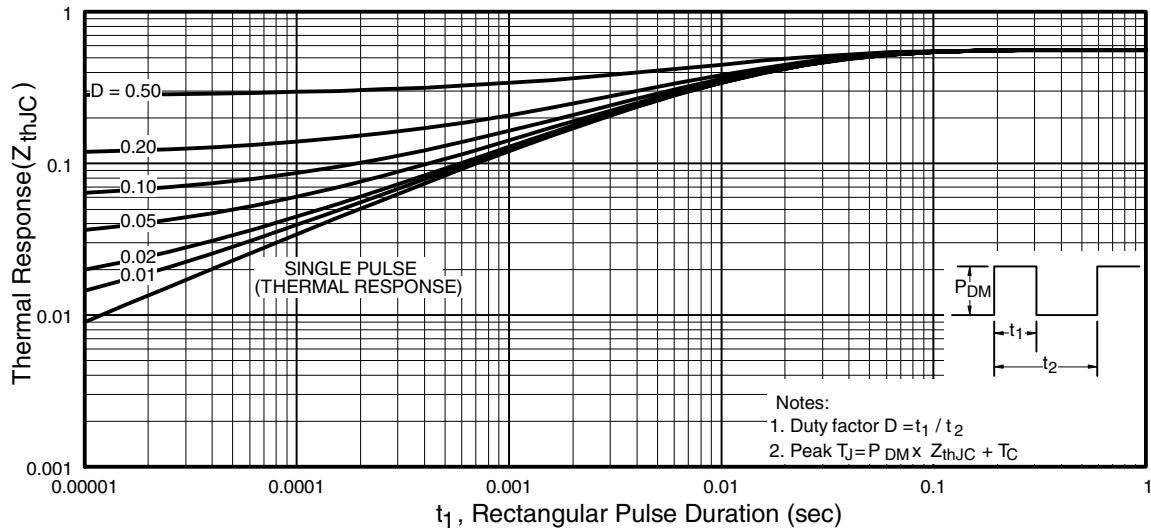


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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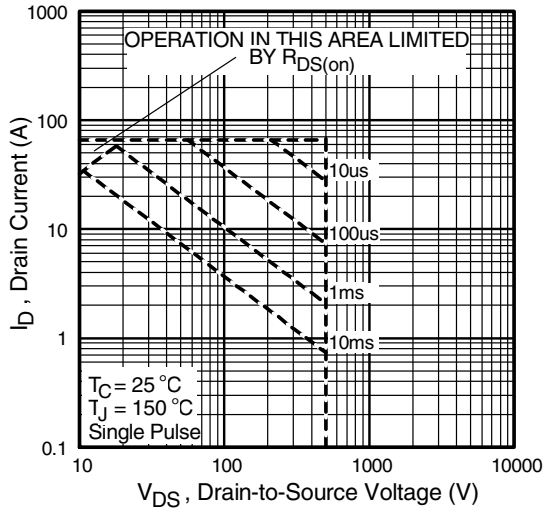


Fig 12. Maximum Safe Operating Area

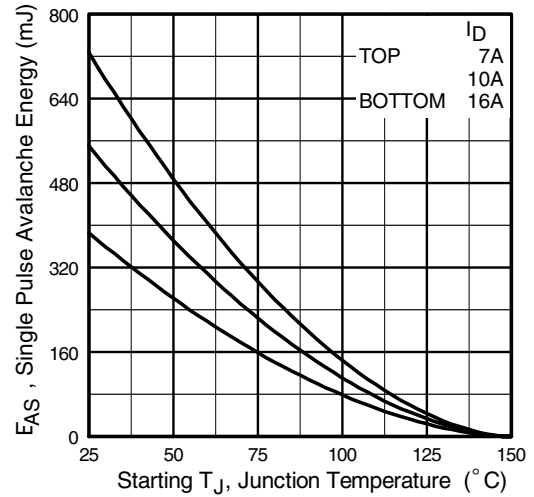


Fig 13. Maximum Avalanche Energy vs. Drain Current

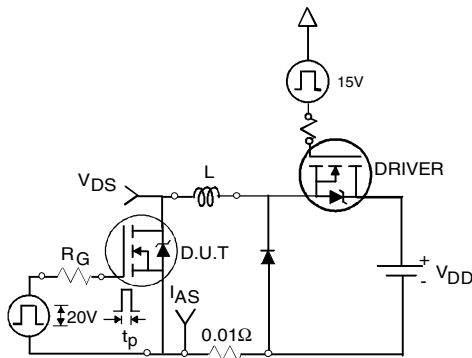


Fig 14a. Unclamped Inductive Test Circuit

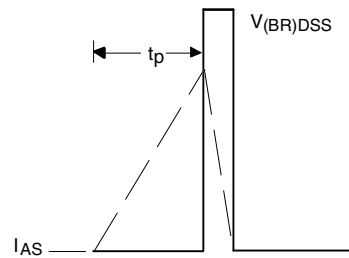


Fig 14b. Unclamped Inductive Waveforms

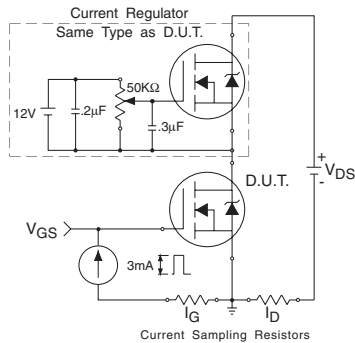


Fig 15a. Gate Charge Test Circuit

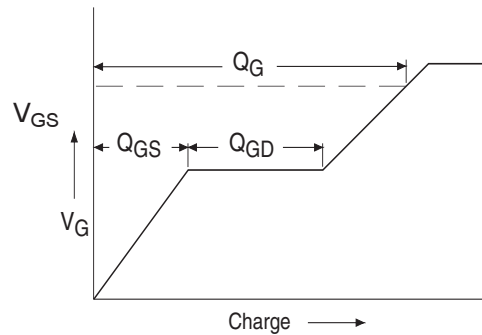
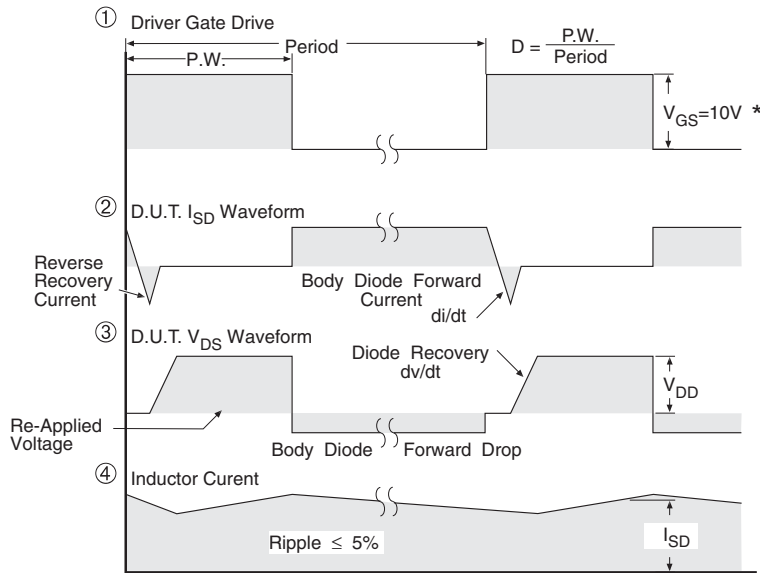
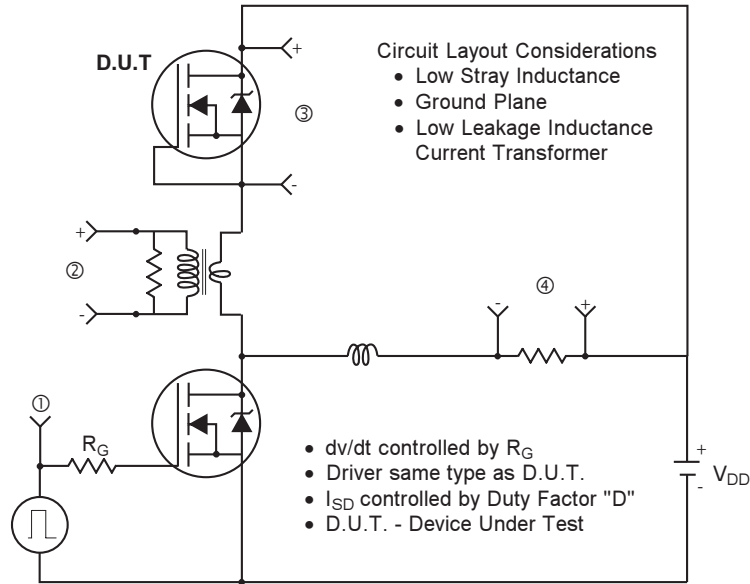


Fig 15b. Basic Gate Charge Waveform

Peak Diode Recovery dv/dt Test Circuit



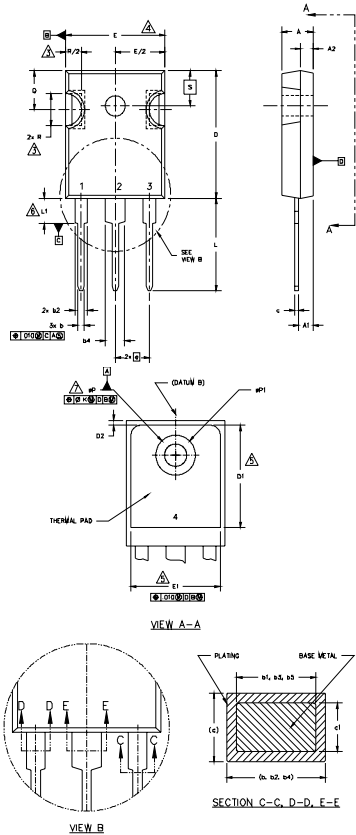
* $V_{GS} = 5V$ for Logic Level Devices

Fig 16. For N-Channel HEXFET® Power MOSFETs

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TO-247AC Package Outline Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ϕP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154" [3.91].

B. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247 WITH THE EXCEPTION OF DIMENSION c.

SYMBOL	INCHES		MILLIMETERS		NOTES	
	MIN.	MAX.	MIN.	MAX.		
A	.183	.209	4.65	5.31		
A1	.087	.102	2.21	2.59		
A2	.059	.098	1.50	2.49		
b	.039	.055	0.99	1.40		
b1	.039	.053	0.99	1.35		
b2	.065	.094	1.65	2.39		
b3	.065	.092	1.65	2.37		
b4	.102	.135	2.59	3.43		
b5	.102	.133	2.59	3.38		
c	.015	.034	0.38	0.86		
c1	.015	.030	0.38	0.76		
D	.776	.815	19.71	20.70		4
D1	.515	-	13.08	-		5
D2	.020	.030	0.51	0.76		4
E	.602	.625	15.29	15.87		
E1	.540	-	15.72	-		
e	.215 BSC		5.46 BSC			
ϕk	.010		2.54			
L	.559	.634	14.20	16.10		
L1	.146	.169	3.71	4.29		
N	3		7.62 BSC			
ϕP	.140	.144	3.56	3.66		
$\phi P1$	-	.275	-	6.98		
O	.209	.224	5.31	5.69		
R	.178	.216	4.52	5.49		
S	.217 BSC		5.51 BSC			

LEAD ASSIGNMENTS

HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

IGBTs, CoPACK

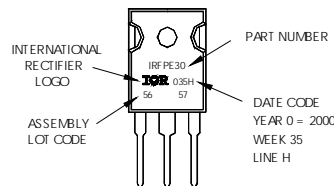
1.- GATE
2.- COLLECTOR
3.- EMITTER
4.- COLLECTOR

DIODES

1.- ANODE/OPEN
2.- CATHODE
3.- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW/35, 2000
IN THE ASSEMBLY LINE "H"
Note: "P" in assembly line
position indicates "Lead-Free"



Data and specifications subject to change without notice.
This product has been designed and qualified for the Automotive [Q101] market.
Qualification Standards can be found on IR's Web site.

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08/04



Notice

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